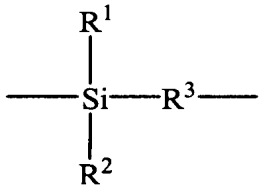
IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): An insulation film having a thickness of from about 0.01 to 3 μm, and comprising an organosilicon polymer with a relative dielectric constant of 4 or less having a dry etching selection ratio to the compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, a spin-on-glass, polyorganosiloxane, and an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin, wherein the organosilicon polymer is at least one polycarbosilane selected from the group consisting of polymers having the structural unit of the following formula (1),



(1)

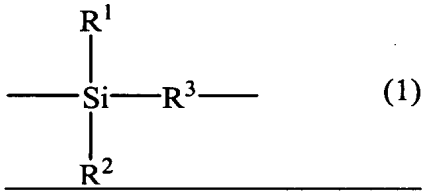
wherein R^1 and R^2 independently represent a hydrogen atom, an alkyl group having 1-30 carbon atoms that may have a substituent, an alkenyl group having 1-30 carbon atoms that may have a substituent, an alkynyl group having 1-30 carbon atoms that may have a substituent, or an aromatic group that may have a substituent and R^3 represents –C≡C–, $-CH_2-$ or fluoro-substituted $-CH_2-$ having a substituent linked with at least one –C≡C– group, an alkylene or fluoro-substituted alkylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkenylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkynylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, or

a divalent aromatic group having 6-30 carbon atoms and having a substituent linked with at least one –C≡C– group.

Claim 2 (Original): The insulation film according to claim 1, wherein the dry etching selection ratio is 1/3 or less.

Claims 3-4 (Canceled).

Claim 5 (Currently Amended): A coating solution composition comprising (I) ~~the organosilicon polymer described in claim 1~~ at least one polycarbosilane selected from the group consisting of polymers having the structural unit of the following formula (1),



(1)

wherein R^1 and R^2 independently represent a hydrogen atom, an alkyl group having 1-30 carbon atoms that may have a substituent, an alkenyl group having 1-30 carbon atoms that may have a substituent, an alkynyl group having 1-30 carbon atoms that may have a substituent, or an aromatic group that may have a substituent and R^3 represents –C≡C–, $-CH_2-$ or fluoro-substituted $-CH_2-$ having a substituent linked with at least one –C≡C– group, an alkylene or fluoro-substituted alkylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkenylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkynylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, or a divalent aromatic group having 6-30 carbon atoms and having a substituent linked with at

least one –C≡C– group, and at least one additive selected from the group consisting of colloidal silica, colloidal alumina, an organic polymer other than the organosilicon polymer, a surfactant, silane coupling agent, and triazene compound, wherein the other polymer is at least one polymer selected from the group consisting of compounds with a sugar chain structure, vinyl amide polymers, (meth)acrylic polymers, aromatic vinyl compound polymers, dendolimers, polyimides, polyamic acids, polyarylene, polyamides, polyquinoxalines, polyoxadizoles, fluorine-containing polymers, and compounds with a polyalkylene oxide structure, and (II) an organic solvent.

Claim 6 (Original): A method of forming an insulating film comprising applying the coating solution composition of claim 5 to a substrate and heating the applied composition.

Claim 7 (Original): A method of forming an insulating film comprising applying the coating solution composition of claim 5 to a substrate and heating the applied composition in the presence of oxygen or peroxide to three-dimensionally crosslink the composition.

Claim 8 (Original): An etching stopper comprising the insulation film described in claim 1 formed below an upper layer film comprising a compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, spin-on glass, and polyorganosiloxane or an upper layer film comprising an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin and having an etch rate of 1/3 or less of the plasma dry etching rate of the upper layer film.

Claim 9 (Original): A hard mask comprising the insulation film described in claim 1 formed on an under layer film comprising a compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, spin-on glass, and polyorganosiloxane or an under layer film comprising an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin and having an etch rate of 1/3 or less of the plasma dry etching rate of the under layer film.

Claim 10 (Previously Presented): A method comprising dry etching an insulation film using the etching stopper of claim 8.

Claim 11 (Previously Presented): A method comprising damascene structure processing using the etching stopper of claim 8.

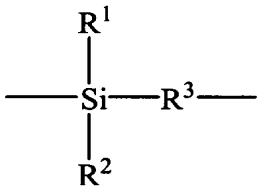
Claim 12 (Previously Presented): A method comprising dual damascene structure processing using the etching stopper of claim 8.

Claim 13 (Previously Presented): A method comprising dry etching an insulation film using the hard mask of claim 9.

Claim 14 (Previously Presented): A method comprising damascene structure processing using the hard mask of claim 9.

Claim 15 (Previously Presented): A method comprising dual damascene structure processing using the hard mask of claim 9.

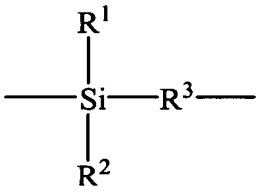
Claim 16 (New): An insulation film comprising an organosilicon polymer with a relative dielectric constant of 4 or less having a dry etching selection ratio to the compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, a spin-on-glass, polyorganosiloxane, and an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin, wherein the organosilicon polymer is at least one polycarbosilane selected from the group consisting of polymers having the structural unit of the following formula (1),



(1)

wherein R^1 and R^2 independently represent an alkyl group having 1-30 carbon atoms that may have a substituent, an alkenyl group having 1-30 carbon atoms that may have a substituent, an alkynyl group having 1-30 carbon atoms that may have a substituent, or an aromatic group that may have a substituent and R^3 represents –C≡C–, -CH_2- or fluoro-substituted -CH_2- having a substituent linked with at least one –C≡C– group, an alkylene or fluoro-substituted alkylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkenylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkynylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, or a divalent aromatic group having 6-30 carbon atoms and having a substituent linked with at least one –C≡C– group.

Claim 17 (New): An insulation film comprising an organosilicon polymer with a relative dielectric constant of 4 or less having a dry etching selection ratio to the compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, a spin-on-glass, polyorganosiloxane, and an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin, wherein the organosilicon polymer is at least one polycarbosilane selected from the group consisting of polymers having the structural unit of the following formula (1),



(1)

wherein R^1 and R^2 independently represent a hydrogen atom, an alkyl group having 1-30 carbon atoms that may have a substituent, an alkenyl group having 1-30 carbon atoms that may have a substituent, an alkynyl group having 1-30 carbon atoms that may have a substituent, or an aromatic group that may have a substituent and R^3 represents –C≡C–, $-CH_2-$ or fluoro-substituted $-CH_2-$ having a substituent linked with at least one –C≡C– group, an alkylene or fluoro-substituted alkylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkenylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkynylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, or a divalent aromatic group having 6-30 carbon atoms and having a substituent linked with at least one –C≡C– group, and wherein said insulation film additionally comprises at least one additive selected from the group consisting of colloidal silica, colloidal alumina, an organic polymer other than the organosilicon polymer, a surfactant, silane coupling agent, and

triazene compound, wherein the other polymer is at least one polymer selected from the group consisting of compounds with a sugar chain structure, vinyl amide polymers, (meth)acrylic polymers, aromatic vinyl compound polymers, dendolimers, polyimides, polyamic acids, polyarylene, polyamides, polyquinoxalines, polyoxadizoles, fluorine-containing polymers, and compounds with a polyalkylene oxide structure.